

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14	(SHIBATA-YOSHIYUKI).in.	US-PGPUB; USPAT	OR	OFF	2005/05/28 23:28
L2	7	((SHIBATA-YOSHIYUKI).in.) and (capacitor dram)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L3	109	(MATSUSHITA-ELECTRICAL-INDUSTRIAL-CO-LTD MATSUSHITA-ELECTRICAL-INDUSTRIAL-COMPANY-LTD MATSUSHITA-ELECTRICAL-INDUSTRIAL-CO MATSUSHITA-ELECTRICAL-INDUSTRIAL MATSUSHITA-ELECTRICAL-CO-LTD MATSUSHITA-ELECTRICMATSUSHITA-ELECTRIAL-INDUSTRIAL-CO-LTD MATSUSHITA-ELECTRC-INDUSTRIAL-CO-LTD MATSUSHITA-ELECTRONICS-CORPORATION).as.	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L4	16	((MATSUSHITA-ELECTRICAL-INDUSTRIAL-CO-LTD MATSUSHITA-ELECTRICAL-INDUSTRIAL-COMPANY-LTD MATSUSHITA-ELECTRICAL-INDUSTRIAL-CO MATSUSHITA-ELECTRICAL-INDUSTRIAL MATSUSHITA-ELECTRICAL-CO-LTD MATSUSHITA-ELECTRICMATSUSHITA-ELECTRIAL-INDUSTRIAL-CO-LTD MATSUSHITA-ELECTRC-INDUSTRIAL-CO-LTD MATSUSHITA-ELECTRONICS-CORPORATION).as.) and (capacitor dram)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L5	0	"10694891"	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L6	1782	((different differing differs differ) adj capacitance)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L7	1529	((((different differing differs differ) adj capacitance)) and (capacitor dram (dynamic adj random adj access)))	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L8	170	((different differing differs differ) adj capacitance) with (first and second)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:30

L9	153	((((different differing differs differ) adj capacitance) with (first and second)) and (capacitor dram (dynamic adj random adj access)))	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L10	143	(((((different differing differs differ) adj capacitance) with (first and second)) and (capacitor dram (dynamic adj random adj access))) not (@ad>"20031029" or @rlad>"20031029"))	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L11	14	(((((different differing differs differ) adj capacitance) with (first and second)) and (capacitor dram (dynamic adj random adj access))) not (@ad>"20031029" or @rlad>"20031029")) and (operat\$ adj voltage)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:35
L12	52	(((((different differing differs differ) adj capacitance) with (first and second)) and (capacitor dram (dynamic adj random adj access))) not (@ad>"20031029" or @rlad>"20031029")) and (memory or dram)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L13	269	(jennifer near2 kennedy).xa.	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L14	3090	"capacitors" with (different differing differs differ) with capacitance	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L15	1667	"capacitors" with (different differing differs differ) with (capacitances capacitance)	US-PGPUB; USPAT	OR	OFF	2005/05/28 23:25
L16	1	("capacitors" with (different differing differs differ) with (capacitances capacitance)) and ((jennifer near2 kennedy).xa.)	US-PGPUB; USPAT	OR	OFF	2005/05/28 23:25
L17	2892	("capacitors" with (different differing differs differ) with (capacitances capacitance)) not (@ad>"20031029" or @rlad>"20031029")	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L18	952	((("capacitors" with (different differing differs differ) with (capacitances capacitance)) not (@ad>"20031029" or @rlad>"20031029")) and (memory or dram)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L19	869	"capacitors" near4 (different differing differs differ) near4 (capacitances capacitance)	US-PGPUB; USPAT	OR	OFF	2005/05/28 23:25

L20	1266	("capacitors" near4 (different differing differs differ) near4 (capacitances capacitance)) not (@ad>"20031029" or @rlad>"20031029")	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L21	456	((("capacitors" near4 (different differing differs differ) near4 (capacitances capacitance)) not (@ad>"20031029" or @rlad>"20031029")) and (memory or dram)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L22	255	((("capacitors" near4 (different differing differs differ) near4 (capacitances capacitance)) not (@ad>"20031029" or @rlad>"20031029")) and (memory or dram)) and semiconductor	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L23	299	((("capacitors" near4 (different differing differs differ) near4 (capacitances capacitance)) not (@ad>"20031029" or @rlad>"20031029")) and (memory or dram)) and (substrate semiconductor)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L24	0	(trench adj capacitor) with "same" with substrate with ((cylindrical cylindrically cup-shap\$ (cup adj shap\$)) near2 capacitor)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L25	165	DRAM with embed\$ with LSI	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L26	143	(DRAM with embed\$ with LSI) not (@ad>"20031029" or @rlad>"20031029")	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L27	496	(high adj speed) with (low adj power) same DRAM	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L28	7	((high adj speed) with (low adj power) same DRAM) and ((different differing differs differ) with (capacitances capacitance))	US-PGPUB; USPAT	OR	OFF	2005/05/28 23:25
L29	13	(((((different differing differs differ) adj capacitance) with (first and second)) and (capacitor dram (dynamic adj random adj access))) not (@ad>"20031029" or @rlad>"20031029")) and (dram)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25

L30	52	((((different differing differs differ) adj capacitance) with (first and second)) and (capacitor dram (dynamic adj random adj access))) not (@ad>"20031029" or @rlad>"20031029")) and (memory or dram)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L31	16	((operate operating) near2 (voltage)) with DRAM with (varies depends dependant)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L32	58	((operate operating) near2 (voltage)) with DRAM with (differ different depends dependant)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L33	58	(((operate operating) near2 (voltage)) with DRAM with (differ different depends dependant)) not (((operate operating) near2 (voltage)) with DRAM with (varies depends dependant))	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L34	57	(((operate operating) near2 (voltage)) with DRAM with (differ different depends dependant)) not (((operate operating) near2 (voltage)) with DRAM with (varies depends dependant))) not (@ad>"20031029" or @rlad>"20031029")	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L35	4	(voltage with DRAM with (differ different depends dependant)with (capacitance))	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L36	299	(((("capacitors" near4 (different differing differs differ) near4 (capacitances capacitance)) not (@ad>"20031029" or @rlad>"20031029")) and (memory or dram)) and (substrate semiconductor)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L37	125	(((("capacitors" near4 (different differing differs differ) near4 (capacitances capacitance)) not (@ad>"20031029" or @rlad>"20031029")) and (memory or dram)) and (substrate semiconductor)) and ((dynamic adj random) dram)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L38	310	(((("capacitors" with (different differing differs differ) with (capacitances capacitance)) not (@ad>"20031029" or @rlad>"20031029")) and (dram)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25

L39	1	("4327476").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/28 23:25
L40	0	((("4327476").PN.) and (dram or (dynamic adj access))	US-PGPUB; USPAT	OR	OFF	2005/05/28 23:25
L41	1	("4118794").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/28 23:25
L42	0	((("4118794").PN.) and (dram or (dynamic adj access))	US-PGPUB; USPAT	OR	OFF	2005/05/28 23:25
L43	143	(DRAM with embed\$ with LSI) not (@ad>"20031029" or @rlad>"20031029")	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L44	101	((DRAM with embed\$ with LSI) not (@ad>"20031029" or @rlad>"20031029")) and (voltage)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L45	1	"20010026835"	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L46	1	"20010026835" and (capacitor voltage dram)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L47	1782	((different differ differing) adj capacitance)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L48	53733	((different differ differing) near2 voltage)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L49	4079	((different differ differing) near2 capacitance)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L50	764	L48 and L49	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L51	128	dram adj section	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L52	1	L51 and L50	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L53	1085	dram near2 section	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L54	4	L53 and L50	US-PGPUB; USPAT	OR	OFF	2005/05/28 23:25
L55	1	("6418044").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/28 23:25
L56	0	L55 and (electrode)	US-PGPUB; USPAT	OR	OFF	2005/05/28 23:25
L57	0	L55 and (electrode)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L58	0	L55 and (plates)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25

L59	15	((different differ differing) near2 capacitance) with "same" with (wafer substrate)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L60	371	(stacked adj capacitor) and (planar adj capacitor)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L61	335	L60 and ("438"/\$.ccls. or "257"/\$.ccls.)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L62	2	(planar adj capacitor) with (dielectric insulat\$) with "same" with (gate near2 (insulat\$ dielectric))	US-PGPUB; USPAT	OR	ON	2005/05/28 23:25
L63	1433	((different differing differs differ) adj capacitance) and (capacitor dram (dynamic adj random adj access))) not (@ad>"20031029" or @rlad>"20031029")	US-PGPUB; USPAT	OR	ON	2005/05/28 23:36
L64	290	63 and ((different differing differs differ) near2 voltage)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:36
L65	6	63 and ((different differing differs differ) near2 voltage near2 operat\$3)	US-PGPUB; USPAT	OR	ON	2005/05/28 23:43
L66	1	("6858513").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/28 23:43
L67	1	66 and voltage	US-PGPUB; USPAT	OR	ON	2005/05/28 23:44